



DC COMPONENTS CO., LTD.

DISCRETE SEMICONDUCTORS

2SB564A

TECHNICAL SPECIFICATIONS OF PNP EPITAXIAL PLANAR TRANSISTOR

Description

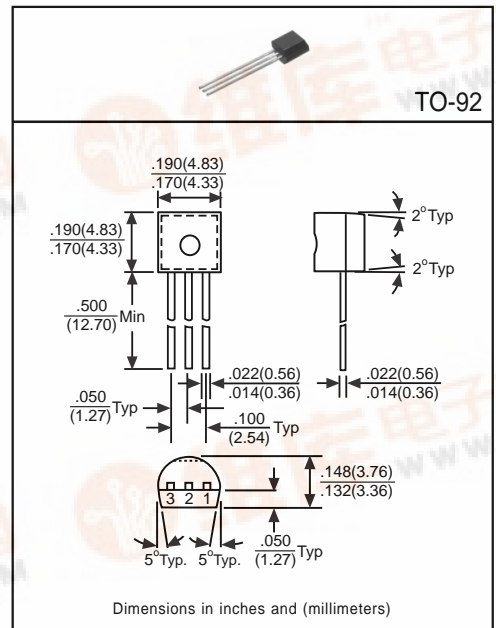
Designed for low frequency power amplifier applications.

Pinning

- 1 = Emitter
- 2 = Collector
- 3 = Base

Absolute Maximum Ratings(T_A=25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V _{CB0}	-30	V
Collector-Emitter Voltage	V _{CEO}	-25	V
Emitter-Base Voltage	V _{EB0}	-5	V
Collector Current	I _C	-1	A
Total Power Dissipation	P _D	800	mW
Junction Temperature	T _J	+150	°C
Storage Temperature	T _{STG}	-55 to +150	°C



Electrical Characteristics

(Ratings at 25°C ambient temperature unless otherwise specified)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
Collector-Base Breakdown Voltage	BV _{CB0}	-30	-	-	V	I _C =-100μA, I _E =0
Collector-Emitter Breakdown Voltage	BV _{CEO}	-25	-	-	V	I _C =-10mA, I _B =0
Emitter-Base Breakdown Voltage	BV _{EB0}	-5	-	-	V	I _E =-100μA, I _C =0
Collector Cutoff Current	I _{CBO}	-	-	-100	nA	V _{CB} =-30V, I _E =0
Collector-Emitter Saturation Voltage ⁽¹⁾	V _{CE(sat)}	-	-	-0.5	V	I _C =-1A, I _B =-100mA
Base-Emitter Saturation Voltage ⁽¹⁾	V _{BE(sat)}	-	-	-1.2	V	I _C =-1A, I _B =-100mA
DC Current Gain ⁽¹⁾	h _{FE}	70	-	400	-	I _C =-100mA, V _{CE} =-1V
Transition Frequency	f _T	-	110	-	MHz	I _C =-10mA, V _{CE} =-6V, f=100MHz
Output Capacitance	C _{ob}	-	18	-	pF	V _{CB} =-6V, f=1MHz

(1)Pulse Test: Pulse Width ≤380μs, Duty Cycle ≤2%

Classification of hFE

Rank	Q	Y	GR
Range	70-140	120-240	200-400

